



V <sub>(BR)DSX</sub> / V <sub>(BR)DGX</sub>	R <sub>DS(on)</sub> (max)	I <sub>DSS</sub> (min)	Package
60V	1Ω	600mA	SOT-89

#### **Features**

 Depletion Mode Device Offers Low R<sub>DS(on)</sub> at Cold Temperatures

Low On-Resistance: 1Ω max. at 25°C

· High Input Impedance

Low V<sub>GS(off)</sub> Voltage: -1.4 to -3.1V
Small Package Size SOT-89

## **Applications**

- Ignition Modules
- Normally-On Switches
- Solid State Relays
- Converters
- Security
- Power Supplies

## **Description**

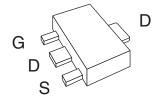
The CPC3701 is an N-channel, depletion mode, field effect transistor (FET) that utilizes IXYS Integrated Circuits Division's proprietary third-generation vertical DMOS process. The third-generation process realizes world class, high voltage MOSFET performance in an economical silicon gate process. Our vertical DMOS process yields a robust device, with high input impedance, for use in high-power applications. The CPC3701 is a highly reliable FET device that has been used extensively in our Solid State Relays for industrial and security applications.

The CPC3701 has a minimum breakdown voltage of 60V, and is available in the SOT-89 package. As with all MOS devices, the FET structure prevents thermal runaway and thermal-induced secondary breakdown.

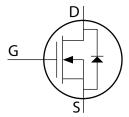
## **Ordering Information**

Part #	Description	
CPC3701CTR	N-Channel Depletion Mode FET, SOT-89 Pkg. Tape and Reel (1000/Reel)	

# Package Pinout (SOT-89)



# **Circuit Symbol**











# Absolute Maximum Ratings @ 25°C

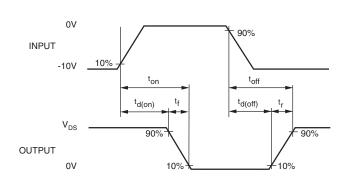
Parameter	Ratings	Units	
Drain-to-Source Voltage	60	$V_{P}$	
Gate-to-Source Voltage	±15	V <sub>P</sub>	
Pulsed Drain Current	1	Α	
Total Package Dissipation 1	1.1	W	
Operational Temperature	-55 to +125	°C	
Storage Temperature	-55 to +125	°C	

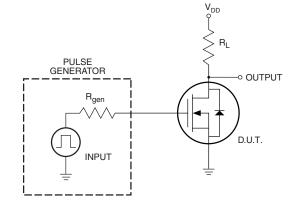
Absolute Maximum Ratings are stress ratings. Stresses in excess of these ratings can cause permanent damage to the device. Functional operation of the device at conditions beyond those indicated in the operational sections of this data sheet is not implied.

## **Electrical Characteristics @ 25°C (Unless Otherwise Noted)**

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSX</sub>	$V_{GS} = -5.5V, I_{D} = 100\mu A$	60	-	-	V
Gate-to-Source Off Voltage	V <sub>GS(off)</sub>	$V_{DS} = 5V, I_{D} = 1 \mu A$	-1.4	-	-3.1	V
Change in V <sub>GS(off)</sub> with Temperature	dV <sub>GS(off)</sub> /dT	$V_{DS} = 5V, I_{D} = 1 \mu A$	-	-	4.5	mV/°C
Gate Body Leakage Current	I <sub>GSS</sub>	$V_{GS}=\pm15V, V_{DS}=0V$	-	-	100	nA
Drain-to-Source Leakage Current	1	V <sub>GS</sub> = -5.5V, V <sub>DS</sub> =60V	-	-	1	μΑ
	I <sub>D(off)</sub>	$V_{GS} = -5V, V_{DS} = 40V, T_A = 125^{\circ}C$	-	-	1	mA
Saturated Drain-to-Source Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> =15V	600	-	-	mA
Static Drain-to-Source On-State Resistance	R <sub>DS(on)</sub>	V = 0V I = 200m A	-	-	1	Ω
Change in R <sub>DS(on)</sub> with Temperature	dR <sub>DS(on)</sub> /dT	$V_{GS} = 0V$ , $I_D = 300 \text{mA}$	-	-	1.1	%/°C
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = 25V		-	70	
Rise Time	t <sub>r</sub>	I <sub>D</sub> = 300mA		-	40	-
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS} = 0V \text{ to -10V}$	-	50	ns	
Fall Time	t <sub>f</sub>	$R_{qen} = 50\Omega$		-	150	
Source-Drain Diode Voltage Drop	V <sub>SD</sub>	V <sub>GS</sub> = -5V, I <sub>SD</sub> =300mA	-	0.6	1.8	V
Thermal Resistance (Junction to Ambient)	$R_{ heta JA}$	-	-	90	-	°C/W

# **Switching Waveform & Test Circuit**

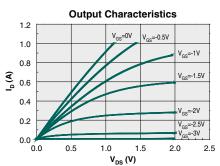


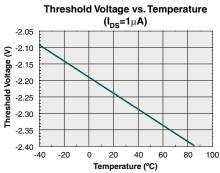


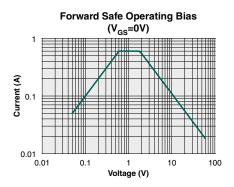
<sup>&</sup>lt;sup>1</sup> Mounted on 1"x1" FR4 board.

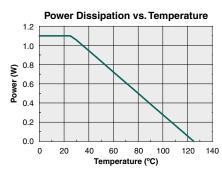


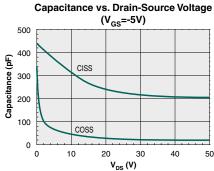
# PERFORMANCE DATA\* @ 25°C (Unless Otherwise Noted)

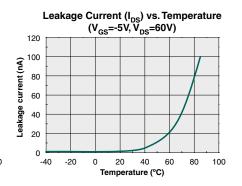


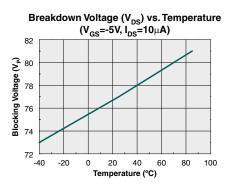












<sup>\*</sup>The Performance data shown in the graphs above is typical of device performance. For guaranteed parameters not indicated in the written specifications, please contact our application department.



## **Manufacturing Information**

## **Moisture Sensitivity**

All plastic encapsulated semiconductor packages are susceptible to moisture ingression. IXYS Integrated Circuits Division classified all of its plastic encapsulated devices for moisture sensitivity according to the latest version of the joint industry standard, IPC/JEDEC J-STD-020, in force at the time of product evaluation. We test all of our products to the maximum conditions set forth in the standard, and guarantee proper operation of our devices when handled according to the limitations and information in that standard as well as to any limitations set forth in the information or standards referenced below.

Failure to adhere to the warnings or limitations as established by the listed specifications could result in reduced product performance, reduction of operable life, and/or reduction of overall reliability.

This product carries a **Moisture Sensitivity Level (MSL) rating** as shown below, and should be handled according to the requirements of the latest version of the joint industry standard **IPC/JEDEC J-STD-033**.

Device	Moisture Sensitivity Level (MSL) Rating
CPC3701C	MSL 1

#### **ESD Sensitivity**



This product is ESD Sensitive, and should be handled according to the industry standard JESD-625.

### **Soldering Profile**

This product has a maximum body temperature and time rating as shown below. All other guidelines of **J-STD-020** must be observed.

Device	Maximum Temperature x Time	Maximum Reflow Cycles
CPC3701C	260°C for 30 seconds	3

#### **Board Wash**

IXYS Integrated Circuits Division recommends the use of no-clean flux formulations. However, board washing to remove flux residue is acceptable, and the use of a short drying bake may be necessary. Chlorine-based or Fluorine-based solvents or fluxes should not be used. Cleaning methods that employ ultrasonic energy should not be used.



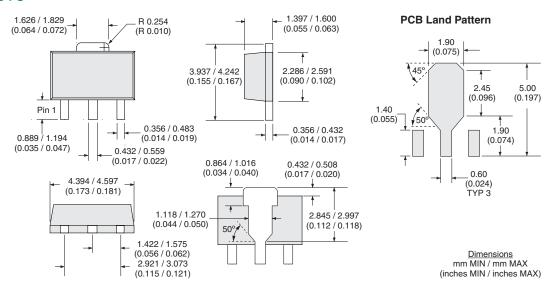




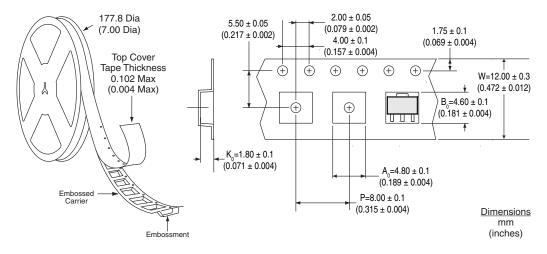


#### **MECHANICAL DIMENSIONS**

### **CPC3701C**



## **CPC3701CTR Tape & Reel**



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